

Product Lineup



Kiru



Kezuru

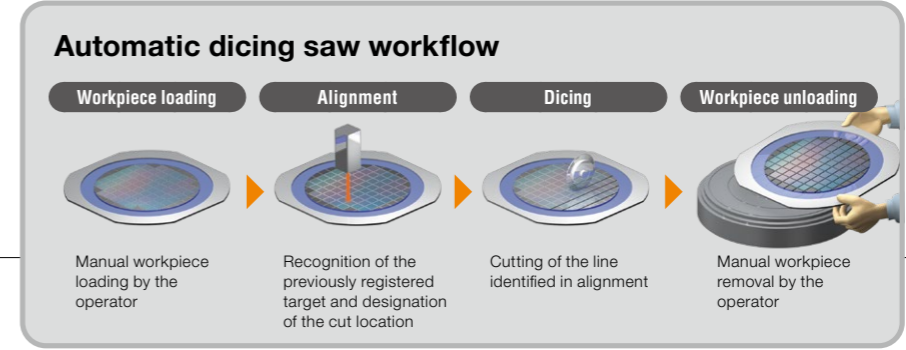


Migaku

Blade Dicing Saw

Automatic Dicing Saw

Automatic cutting and manual handling



DAD324

Compact model for ø150 mm wafers



DAD3221

Standard automatic model for ø150 mm wafers



DAD3231

Highly flexible configuration to meet processing needs



DAD3431

High precision model with X-axis air slider



DAD3241

Standard automatic model for ø200 mm wafers



DAD3351

Flexibility for diverse application needs



DAD3651

Ultracompact facing dual configuration



DAD3361

Highly extensible equipment for ø300 mm and 250x250 mm workpieces

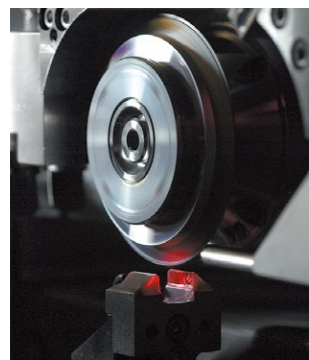


DAD3661

Dual spindle mounted equipment with support for processing large package substrates

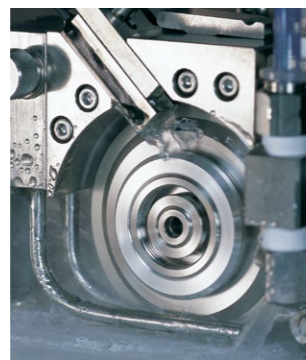
Max workpiece size		mm	ø150	ø150	ø150	ø150	ø200	ø200	ø200	ø200	ø300	ø360/□360
Spindle	Layout		Single	Single	Single	Single	Single	Single	Facing dual spindle	Single	Facing dual spindle	Facing dual spindle
	Output	kW	2.0 at 40,000 min ⁻¹	2.0 at 40,000 min ⁻¹	2.0 at 40,000 min ⁻¹	2.0 at 40,000 min ⁻¹	1.8 at 60,000 min ⁻¹	1.8 at 60,000 min ⁻¹	1.8 at 60,000 min ⁻¹	1.8 at 60,000 min ⁻¹	1.8 at 60,000 min ⁻¹	1.8 at 60,000 min ⁻¹
	Max revolution speed	min ⁻¹	40,000	40,000	40,000	40,000	60,000	60,000	60,000	60,000	60,000	60,000
X-axis	Max cutting speed	mm/sec	0.1 - 800	0.1 - 800	0.1 - 800	0.1 - 300	0.1 - 800	0.1 - 1,000	0.1 - 1,000	0.1 - 1,000	0.1 - 1,000	0.1 - 1,000
Y-axis	Index step	mm	0.0001	0.0001	0.0001	0.0001	0.0001	0.0001	0.0001	0.0001	0.0001	0.0001
	Positioning accuracy	mm	Within 0.005 / 160	Within 0.005 / 160	Within 0.005 / 160	Within 0.0015 / 160	Within 0.002 / 210	Within 0.002 / 260	Within 0.002 / 260	Within 0.002 / 310	Within 0.002 / 400	
Z-axis	Repeating accuracy	mm	0.001	0.001	0.001	0.001	0.001	0.001	0.001	0.001	0.001	
Utilities	Dimensions (WxDxH)	mm	490 × 870 × 1,670	490 × 870 × 1,670	650 × 950 × 1,670	730 × 900 × 1,670	650 × 950 × 1,670	880 × 1,000 × 1,800	790 × 790 × 1,800	880 × 1,000 × 1,800	1,350 × 1,200 × 1,800	
	Weight	kg	Approx. 420	Approx. 420	Approx. 550	Approx. 600	Approx. 550	Approx. 1,100	Approx. 1,040	Approx. 1,100	Approx. 1,550	

Optional Accessories



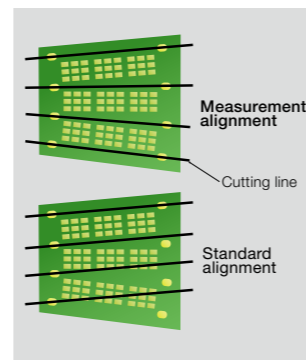
Noncontact setup

Blade tip position relative to the chuck table surface is detected by an optical sensor. Processing quality is stable since the blade wear can be measured at any time during processing.



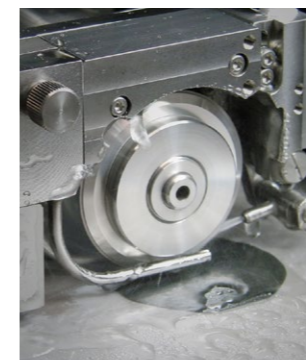
Blade breakage sensor

Processing is stopped immediately if blade breakage occurs to minimize potential workpiece damage.



Measurement alignment

Detects the correct cutting location for workpieces with cutting lines that are not properly aligned due to warpage from baking and curing steps.



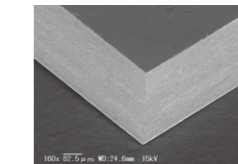
Ultrasonic-wave dicing unit

Ultrasonic-wave pulses promote active self-sharpening of the blade to ensure high quality and high speed processing of difficult to-cut materials such as SiC and glass.

U09 U18

Special blade for ultrasonic-wave dicing
• Blade with built-in oscillator

Application example



SiC Wafer thickness: 350 μm

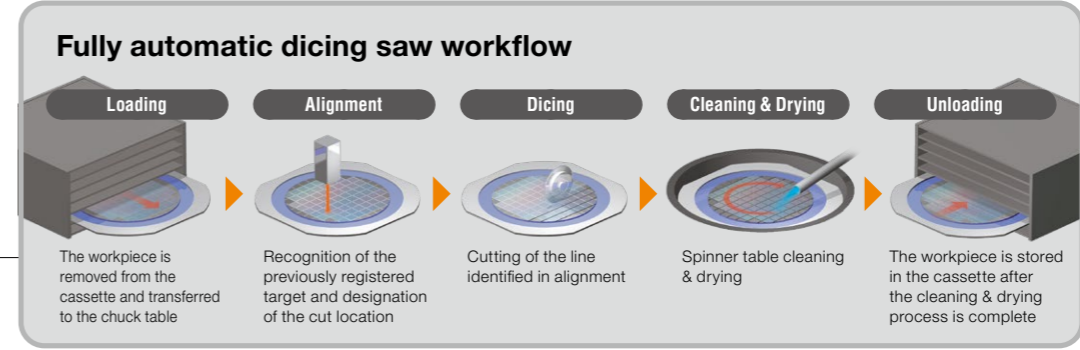


Applicable material	SiC, glass, alumina ceramic, etc.
Bond type	Electroformed

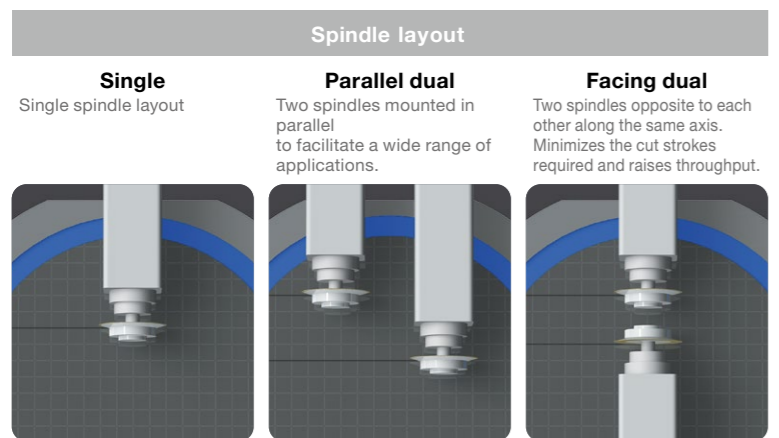
Blade Dicing Saw

Fully Automatic Dicing Saw

Automatic wafer transfer, alignment, cutting, and cleaning & drying



	DFD6240 Reduced-footprint fully automatic single-spindle dicing saw for ø200 mm wafers	DFD6341 Standard equipment which supports ø200 mm wafer processing	DFD6450 Next generation parallel dual dicing saw for a wide range of applications	DFD6363 2-way transfer* flagship model Also supports DBG half-cuts	DFD6561 Space-saving with a reduced maintenance area	DFD6760 Dual chuck table configuration to minimize standby time for maximum efficiency		
Max workpiece size	mm ø200	mm ø200	mm ø200	mm ø300	mm ø300	mm ø300	Max workpiece size	
Spindle	Layout	Single	Facing dual	Parallel dual	Facing dual	Facing dual	Spindle	
	Output	1.2 at 60,000 min ⁻¹	1.2 at 60,000 min ⁻¹	1.0 at 60,000 min ⁻¹	1.8 at 60,000 min ⁻¹	1.8 at 60,000 min ⁻¹		Output
	Max revolution speed	60,000 min ⁻¹	60,000 min ⁻¹	60,000 min ⁻¹	60,000 min ⁻¹	60,000 min ⁻¹		Max revolution speed
X-axis	Feed speed range	0.1 - 600 mm/sec	0.1 - 1,000 mm/sec	0.1 - 600 mm/sec	0.1 - 1,000 mm/sec	0.1 - 1,000 mm/sec	X-axis	
Y-axis	Index step	0.0001 mm	0.0001 mm	0.0001 mm	0.0001 mm	0.0001 mm	Y-axis	
	Positioning accuracy	Within 0.003 / 210 mm	Within 0.002 / 210 mm	Within 0.003 / 250 mm	Within 0.002 / 310 mm	Within 0.002 / 310 mm		Positioning accuracy
Z-axis	Repeating accuracy	0.001 mm	0.001 mm	0.001 mm	0.001 mm	0.001 mm	Z-axis	
Utilities	Dimensions (WxDxH)	900 × 1,190 × 1,800 mm	1,180 × 1,080 × 1,820 mm	1,120 × 1,500 × 1,600 mm	1,200 × 1,550 × 1,800 mm	1,240 × 1,550 × 1,960 mm	Utilities	
	Weight	Approx. 1,200 kg	Approx. 1,500 kg	Approx. 1,400 kg	Approx. 1,800 kg	Approx. 1,500 kg		Weight



Optional Accessories

Cassette and tape frame

High precision products to facilitate stable production from tape moulder to die bonder. Meets the ø300 mm wafer SEMI standard.

Automatic blade changer

Conducts blade change and resumes cutting fully automatically. Minimizes the labour required and raises the utilization rate of the equipment.

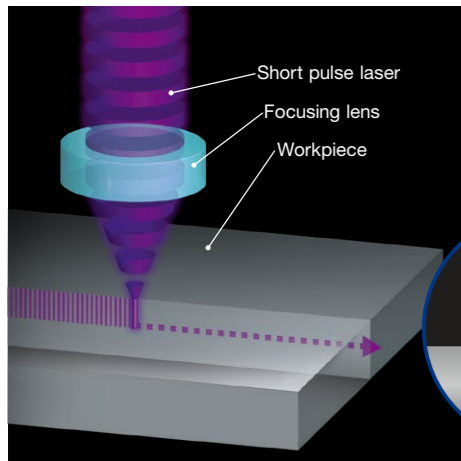
Note: Please consult a DISCO sales representative for information regarding which optional accessories are supported for each model.

DBG
Dicing Before Grinding

What is DBG?
The reverse of the conventional "Backside grinding Wafer cutting" process. Wafer half cut is performed first, then the die are separated through backside grinding. Die can be produced from large-diameter wafers by minimizing backside chipping and wafer damage during die separation (dicing).

Partial Cut Dicing → BG Tape Laminating → Back Grinding → Frame Mounting → BG Tape Peeling

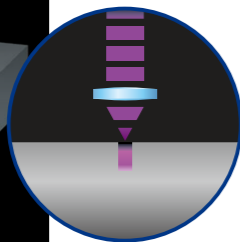
Laser Saw



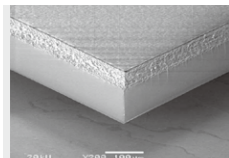
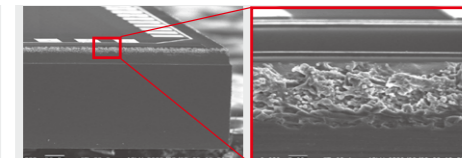
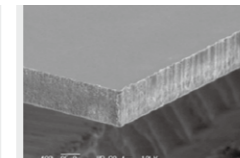
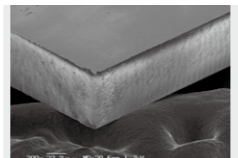
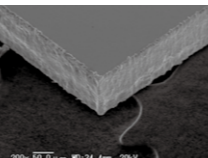
Ablation Process

A processing method utilizing high-intensity laser irradiation in brief intervals to perform cutting.

- Little to no heat damage to the workpiece.
- Non-contact processing with low impact and load.
- Ideal for hard workpieces that are very difficult to process.
- Able to reduce streets down to 10 μm in width. (depends on workpiece conditions)



Ablation process example

Scribing	Grooving	Full cut		
 Sapphire Wafer thickness: 150 μm	 Low-k Wafer thickness: 200 μm Feed speed: 600 mm/s π cut	 Si Wafer thickness: 50 μm Feed speed: 500 mm/s 3 passes	 GaAs Wafer thickness: 100 μm Feed speed: 140 mm/s 1 pass	 Cu-Mo-Cu Wafer thickness: 120 μm



DFL7161

High product quality and high throughput grooving



DFL7160

Supports DAF cutting after DBG

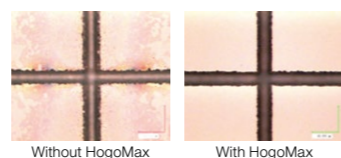
Max workpiece size	mm	ø300	ø300
Processing method		Fully automatic	Fully automatic
X-axis Max feed speed	mm	1.0 - 1,000	0.1 - 600
Y-axis Positioning accuracy	mm	Within 0.003 / 310	Within 0.003 / 310
Utilities Dimensions (WxDxH)	mm	1,560 × 1,550 × 1,800	1,200 × 1,550 × 1,800
Utilities Weight	kg	Approx. 2,300	Approx. 1,750

HogoMax

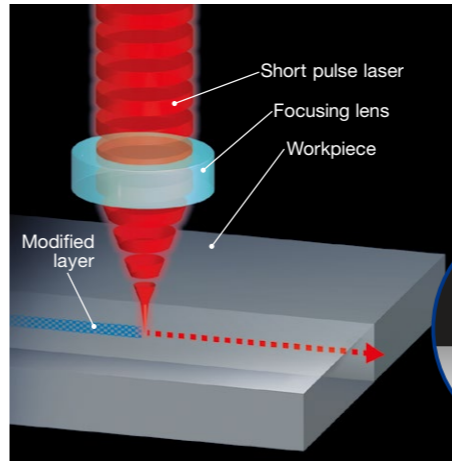
HogoMax

Water soluble protective film to prevent debris adhesion to the wafer surface during ablation

Applying HogoMax to the device surface reduces thermal adhesion of debris from laser ablation to increase reliability and yield.



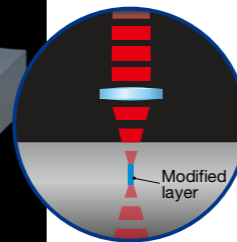
Max workpiece size	mm	ø200	ø300	ø300
Processing method		Fully automatic	Fully automatic	Fully automatic
X-axis Max feed speed	mm	1.0 - 1,000	0.1 - 2,000	1.0 - 1,000
Y-axis Positioning accuracy	mm	Within 0.003 / 210	Within 0.003 / 310	Within 0.003 / 310
Utilities Dimensions (WxDxH)	mm	950 × 1,732 × 1,800	1,600 × 2,755 × 1,800	1,100 × 2,100 × 1,990
Utilities Weight	kg	Approx. 1,800	Approx. 2,850	Approx. 2,090



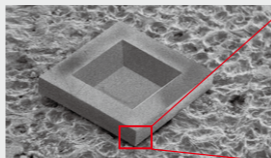
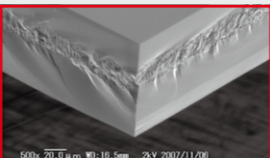
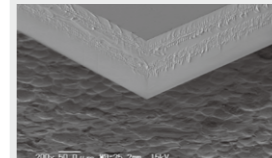
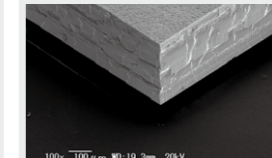
Stealth Dicing

A processing method that focuses a laser within the workpiece to form a modified layer. Die separation is achieved with a tape expander.

- Controls cutting waste because only a subsurface layer is processed. This is suitable for workpieces that are vulnerable to contamination.
- A dry process that does not require cleaning, suitable for applications (such as MEMS) that are vulnerable to mechanical load.
- Extremely narrow kerf widths allow significant reductions in street width.



Stealth dicing process example

 MEMS (Si) Wafer thickness: 100 μm	 Sapphire Wafer thickness: 150 μm	 LiTaO ₃ Wafer thickness: 350 μm	 Glass Wafer thickness: 700 μm
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DFL7341

Realizes high productivity for sapphire and MEMS processing



DFL7362

High-speed, high-quality processing of ultra-thin Si Supports a variety of processes

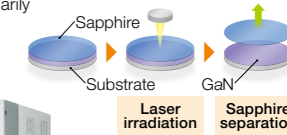


DFL7360FH

Dedicated tape frame transfer model

Laser Lift-Off process

Laser Lift-Off is a process for peeling substrates made of sapphire or glass. It is used for the purpose of peeling off the sapphire substrate from the crystal layer of a GaN (gallium nitride) compound material, primarily used for making vertical structured blue LEDs.



DFL7560L

Laser Lift-Off model with a fixed laser

Max workpiece size	mm	ø150
Utilities Dimensions (WxDxH)	mm	2,000 × 1,810 × 1,800
Utilities Weight	kg	Approx. 3,300

Related Products

Die Separator

High precision die separation after laser processing

DDS2010

Small die separation by breaking

DDS2300

High precision DAF separation

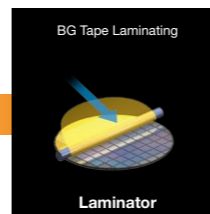
DDS2310

Supports small die separation for ø300 mm wafers

Max workpiece size	mm	ø200	ø300	ø300
Utilities Dimensions (WxDxH)	mm	718 × 897 × 1,608	1,200 × 1,550 × 1,800	1,200 × 1,800 × 1,955
Utilities Weight	kg	Approx. 450	Approx. 900	Approx. 1,000

SDBG

Stealth Dicing Before Grinding



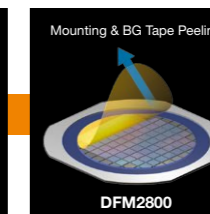
Laminator



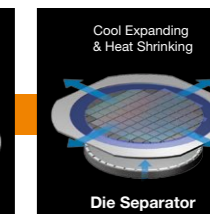
DFL7362



DGP8761



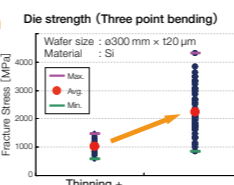
DFM2800



Die Separator

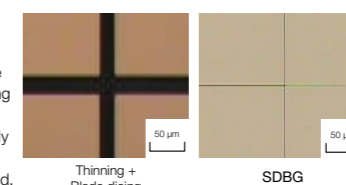
High die strength process

Due to removal of the modified layer created with a laser through grinding, ultrathin, high-strength die can be created



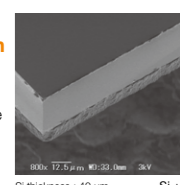
Increase in die yield per wafer

Stealth dicing does not require space on the wafer to be allocated for cutting as the kerf width is almost 0. As a result, street width can be greatly reduced and the number of die obtainable per wafer can be increased.



High quality DAF separation

High grade DAF separation in combination with the Die Separator



Grinder, Polisher, and Surface Planer



Grinder

High precision ultrathin backgrinding



DAG810

A compact and versatile automatic single spindle grinder



DFG8340

Supports small-volume grinding with high precision

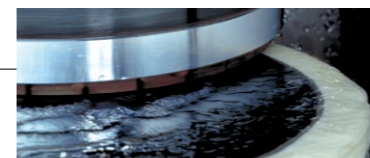


DFG8540

Standard dual-spindle grinder



DFG8560



Grinder / Polisher

Wafer backgrinding and polishing



DFG8830

Quad-spindle grinder designed to process hard materials such as sapphire and SiC



DFG8640

High-precision dual-axis equipment which supports hard and brittle materials including LiTaO₃ and SiC



DGP8761

Integrated backgrinding and stress relief for both enhanced productivity and ultrathin processing
The DFP8761HC supports high cleaning processes for applications such as TSV.

Polisher

Equipment for polishing wafer backsides



DFP8141

CMP polisher specialized for processing hard and brittle materials such as sapphire and SiC



DFP8140

Realizes chemical-free dry polish stress relief

Max workpiece size		mm	ø200	ø200	ø200	ø300	ø150	ø200	ø300	ø200	ø200
Spindle	Number of axes		1	1	2	2	4	2	3	1	1
	Output	kW	4.2	4.2	4.2	4.8	6.3	6	6.3	7.5	4.8
	Revolution speed	min ⁻¹	1,000 - 7,000	1,000 - 7,000	1,000 - 7,000	1,000 - 4,000	1,000 - 4,000	1,000 - 7,000	1,000 - 4,000 (Z1, Z2), 1,000 - 3,000 (Z3)	500 - 2,000	1,000 - 4,000
Number of chuck tables			1	2	3	3	5	3	4	2	1
Utilities	Dimensions (WxDxH)	mm	600 × 1,700 × 1,780	800 × 2,450 × 1,800	1,200 × 2,670 × 1,800	1,400 × 3,322 × 1,800	1,400 × 2,500 × 2,000	1,000 × 2,800 × 1,800	1,690 × 3,315 × 1,800	900 × 2,584 × 2,000	1,200 × 2,670 × 1,800
	Weight	kg	Approx. 1,300	Approx. 2,500	Approx. 3,100	Approx. 4,000	Approx. 6,000	Approx. 3,500	Approx. 6,700	Approx. 3,100	Approx. 1,900

Surface Planer

Ultrahigh-precision planarization of ductile materials using a diamond bit



DAS8920

Compact automatic models ideal for small lot production and R&D



DAS8930



DFS8910

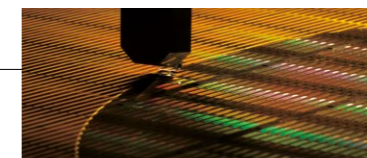
Fully-automatic model for ø200 mm wafers



DFS8960

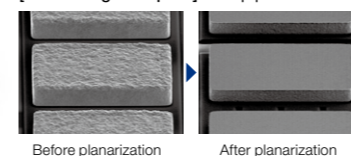
Fully-automatic dual spindle model for ø300 mm wafers

Max workpiece size		mm	ø200	ø300	ø200	ø300
Spindle	Number of axes		1	1	1	2
	Revolution speed	min ⁻¹	100 - 5,000	100 - 5,000	100 - 5,000	100 - 5,000
Number of chuck tables			1	1	1	2
Utilities	Dimensions (WxDxH)	mm	500 × 1,235 × 1,800	730 × 1,570 × 1,800	1,200 × 2,670 × 1,800	1,400 × 3,312 × 1,870
	Weight	kg	Approx. 800	Approx. 1,600	Approx. 2,400	Approx. 5,000

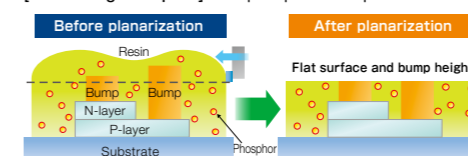


Surface planer processing example

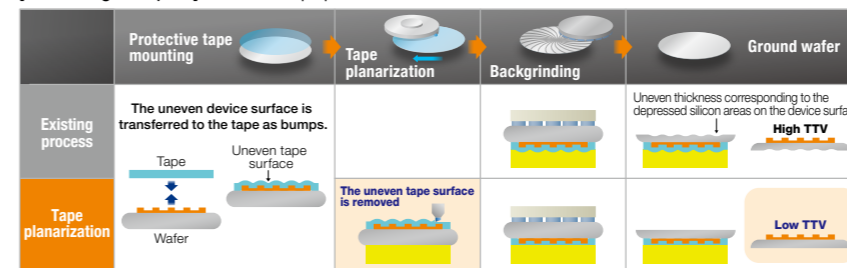
[Processing example 1] Bump planarization



[Processing example 2] LED phosphor resin planarization



[Processing example 3] Protective tape planarization



Related Products

Multifunction Wafer Mounter

An integrated solution for DAF frame mounting and protective tape peeling from thinned wafers.



Image of the DGP8761 in-line system

DFM2800

High-yield thin wafer processing

Max workpiece size		mm	ø300
Utilities	Dimensions (WxDxH)	mm	2,150 × 2,643 × 1,800
	Weight	kg	Approx. 3,100

Dicing Blade

Hub Blade

The combination of an ultra-thin diamond blade and an aluminum hub provides enhanced operational efficiency and stable cutting results



Hubless Blade

Bond type, blade thickness, grit size and outer diameter can be selected to meet processing requirements for a variety of workpieces such as silicon, glass or ceramics.



ZHO5

High-precision concentration control for extremely stable and consistent process results

- Optimized to balance blade life and process quality.

ZH14

Achieves stable processing under high load conditions through use of the high strength V1 bond

- Suppresses breakage and wavy cutting even during high speed and deep cutting or when using blades with long blade exposure

ZHZZ

Ultrathin hub blades for stable dicing of narrow street wafers

- The thinnest hub blades in the industry - only 10 μm wide.

Concentration range

Conventional blade: Low to High
ZHO5: 50, 70, 90, 110, 130

Cut quality comparison (silicon, 0.9 mm thickness)

Conventional blade Kerf 40 μm, Conventional blade Kerf 20 μm, ZHZZ Kerf 10 μm

Applicable material	Silicon, compound semiconductor (GaAs, GaP, etc.), etc.	Applicable material	Silicon, etc.	Applicable material	Silicon, compound semiconductor (GaAs, GaP, etc.), etc.
Bond type	Electroformed	Bond type	Electroformed	Bond type	Electroformed

Z05

Ultra-high cutting performance for a wide range of workpieces and applications

- Through improved fine control of abrasive concentrations, our lineup now offers up to six different concentration levels.

Z09

Electroformed blades optimized for high quality cutting with fine grit sizes

- High-strength bond for high-speed and high-straightness.

ZP07

Porous blade structure for high-grade processing of hard and composite materials

- Dicing solution for SiC and other difficult-to-cut materials.

Concentration range

Conventional blade: Low to High
Z05: 30, 60, 90, 120, 150, 180

PZT processing

Conventional blade, Z09

Blade tip

Grit, Pore
New porous structure electroformed blade

Applicable material	Chip LED board, green ceramics, hard and brittle material, etc.	Applicable material	PZT, LiTaO ₃ , ceramics, silicon, etc.	Applicable material	Composite materials, ceramics, etc.
Bond type	Electroformed	Bond type	Electroformed	Bond type	Electroformed

ZHCR

Designed to prevent blade tip collapse

- Strengthened blade structure to prevent blade tip collapse when processing with blades thicker than 60 μm.

ZHFX

Designed for continuous processing of oxide wafers

- Significantly lowers dress frequency during processing for high continuous processing performance.

ZHDG

Electroformed hub blades for high quality substrate dicing

- Selectable from a lineup with an abundant variety of grit sizes and concentrations.

Blade tip shape and groove comparison

Blade tip, Groove, Collapse
Conventional blade, ZHCR

LiTaO₃ processing

Conventional blade, ZHFX

ZHDG series

ZHDG Series: For substrates #380~#1000
ZHO5 Series: For semiconductor wafers #1500~#5000

Applicable material	Silicon, etc.	Applicable material	Oxide wafers (LiTaO ₃ , etc.)	Applicable material	Chip LED board, semiconductor packages, etc.
Bond type	Electroformed	Bond type	Electroformed	Bond type	Electroformed

R07

High-quality, high-speed cutting of hard and brittle materials

- Utilizes a newly-developed bond material to match the characteristics of the workpiece.

B1A

For precision dicing of difficult-to-cut materials

- Wide variety of bond types for various applications.

TM11

Realizes high blade strength through use of a special bond type

- Supports processes requiring long blade exposures with a thin blade

Bond comparison

Long Blade life, Good Cutting quality
BB500, BB300, BB101, BB200

Applications by grit size

Grit size			
#4500	#2000	#1200	#600 #320
Single crystal ferrite	Ferrite composite	TiO ₂	Glass family (quartz, soda glass etc.)
			Al ₂ O ₃
			Green ceramics
			IC packages
			Sapphire

Position of TM11 blades

Small Blade wear, High Stiffness
Resin, Metal, Electroformed, TM11

Applicable material	Glass, quartz, ceramics, etc.	Applicable material	Electronic parts, optical component material, IC packages, etc.	Applicable material	Green ceramics, IC packages, etc.
Bond type	Resin	Bond type	Metal	Bond type	Metal

Related Products

Color Case, Case Holder for Hub/Hubless Blade



Color Case

Cases for hub and hubless blades which prevent blade mounting errors. Using color cases, the possibility of blade mounting errors can be reduced when different types of blades are used for each equipment and spindle.



Case Holder

Case holders can be attached to the equipment to hold the cases for the blades being used. Using the same color holders and cases improves blade type recognition. These can be used for both hub and hubless blades.



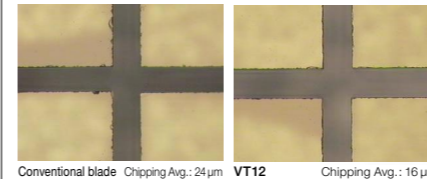
VT07/VT12

High straightness and dimensional accuracy for high-load processing

- Ideal for high quality edge trimming and processing of hard ceramics, sapphire and SiC.



SiC processing



Grinding Wheel



GF13

Improved productivity and grinding quality
Grinding wheel for semiconductor wafers

- Supports SDBG processing



GFCP

Simultaneous grinding of different materials
Wheel for package grinding

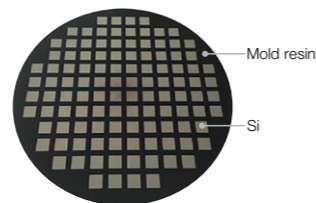
- Supports package grinding with various specifications using customizable vitrified bonds.



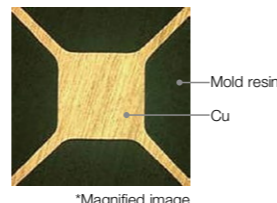
Product lineup

Applications		Bond	Grit size
Silicon	Rough grinding	Resin	SDC340, SD340
		Vitrified (SDBG processing)	SD400, SD600
	Fine grinding	Resin	SD2000
		Vitrified	SD4800, SD6000, 45D

Example of Si + mold resin grinding



Example of Cu + mold resin grinding



*Magnified image

Applicable material: Silicon, SiC, LiTaO₃, GaAs

Applicable material: Semiconductor packages, etc. (composite materials, such as silicon, resin, metal)

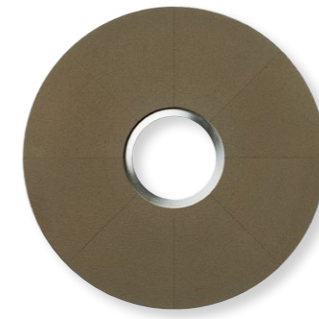
Dry Polishing Wheel



DP08

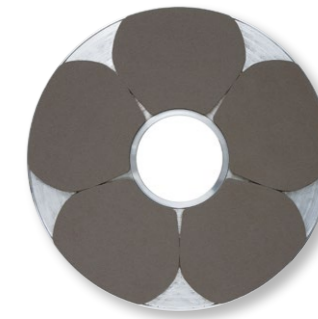
For chemical-free stress relief

- Support for the Dicing Before Grinding process (DBG) as well as normal wafer polishing.

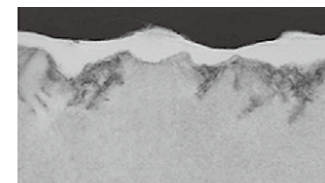


Gettering DP

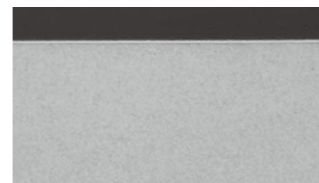
High die strength equal to normal processing while maintaining gettering performance



TEM damage comparison

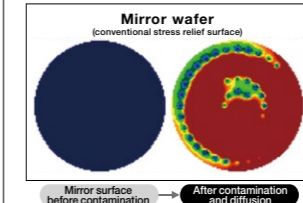


Ground using a #2000 wheel

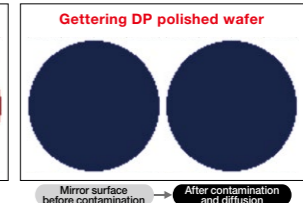


DP08

Gettering effect



Mirror surface before contamination → After contamination and diffusion



Mirror surface before contamination → After contamination and diffusion



Applicable material: Silicon

Applicable material: Silicon

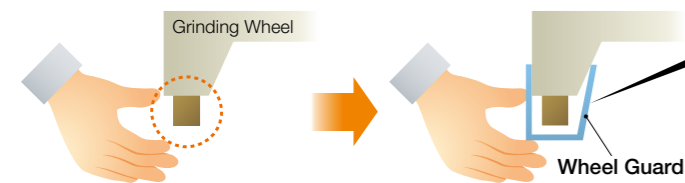
Applicable material: Silicon

Applicable material: Silicon

Related Products

Wheel Guard

Protects wheel segments for streamlined wheel replacement and easier handling.



Without careful handling, some wheel segments may crack or break.

Wheel Guard protects grinding wheel segments to prevent damage.



ø200 mm Wheel Guard



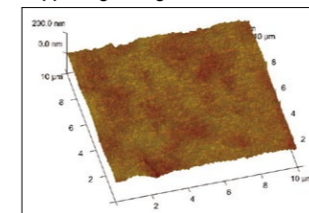
ø300 mm Wheel Guard

Processing examples of various materials (Surface roughness data)

*Data measured using AFM

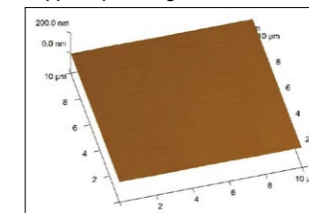
Proven track record of grinding and polishing various materials in addition to silicon

Sapphire grinding



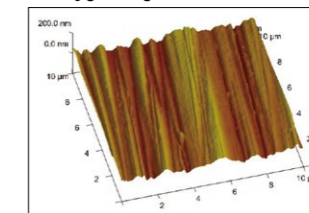
Ra: 10 nm
Ry: 72 nm

Sapphire polishing



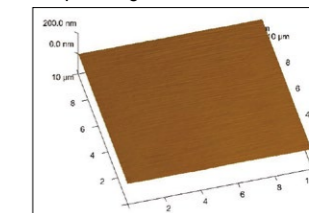
Ra: 1 nm
Ry: 5 nm

LiTaO₃ grinding



Ra: 18 nm
Ry: 106 nm

SiC polishing



Ra: 1 nm
Ry: 6 nm



Deionized Water Recycling Unit

DWR1710 DWR1722

Multi-function, super-compact deionized water recycling unit for dicing saws

- Integrates deionized water production, water temperature control, filtration and cutting water treatment.
- 99% recycling rate (zero wastewater) significantly reduces city water consumption.



		DWR1710	DWR1722
Cutting water	Specific resistance value after treatment MΩ·cm	12 or higher	
	Pumping capacity L/min	10	25
Spindle coolant water system	Pumping capacity L/min	N/A	10
	Temperature setting range °C	20 - 25*	20 - 25
Temperature fluctuation range °C		Within 1*	Within 1
Utilities	Dimensions (WxDxH) mm	780 × 400 × 1,450	450 × 1,600 × 1,656
	Dry weight kg	Approx. 200	Approx. 460

*When the prepared cooling water temperature is -2 °C lower than the set temperature.

Automatic cleaning system

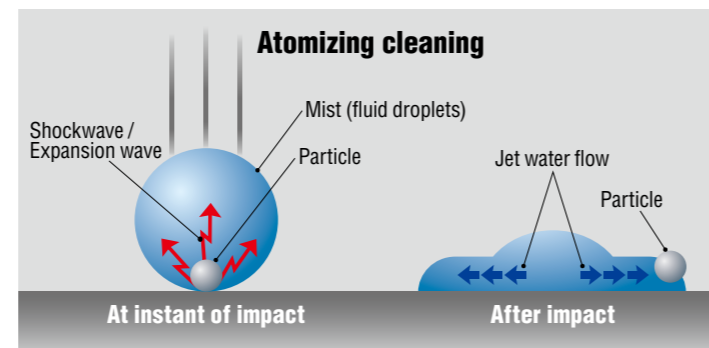
DCS1441 DCS1460

Performs spin cleaning and drying of workpieces processed with an automatic dicing saw

- The highly effective atomizing cleaning nozzle can be installed as an option.
- The cleaning sequence can be fully optimized for any workpiece.



		DCS1441	DCS1460
Max workpiece size	mm	ø200	ø300
	Utilities		
Dimensions (WxDxH) mm		400 × 600 × 1,380	500 × 650 × 1,220
	Dry weight kg	Approx. 120	Approx. 144



Water Temperature Control Unit

DTU152/DTU162 DTU1540/DTU1550

Optimizes the temperature and pressure of both cutting and cooling water

- Complete water temperature regulation to enhance processing accuracy.
- Significantly reduced water consumption by recirculating cutting water via a particle filtration system. (DTU162)



		DTU152	DTU162
Cutting water system	Cooling and heating capacity kW	6.3, 12.5	0.6, 2
	Pumping capacity L/min	25	10
Spindle coolant system	Cooling and heating capacity kW	1.16, 2.5	0.6, 0.6
	Cooling capacity L/min	6	6
Temperature setting range (Cutting water / Spindle coolant water) °C		15 - 30	15 - 30
Temperature fluctuation range °C		Within 1	Within 1
Utilities	Dimensions (WxDxH) mm	450 × 1,296 × 1,235	430 × 900 × 1,500
	Dry weight kg	Approx. 310	Approx. 240

		DTU1540	DTU1550
Cutting water system	Cooling and heating capacity kW	9.4, 10	6.2, 12.5
	Pumping capacity L/min	45	30
Spindle coolant system	Cooling capacity kW	Shared with cutting water	
	Cooling capacity L/min	18	
Temperature setting range (Cutting water / Spindle coolant water) °C		15 - 30	15 - 30
Temperature fluctuation range °C		Within 1	Within 1
Utilities	Dimensions (WxDxH) mm	500 × 780 × 1,650	450 × 1,090 × 1,680
	Dry weight kg	Approx. 270	Approx. 310

Cutting Water Filtration Unit for Dicing Saws

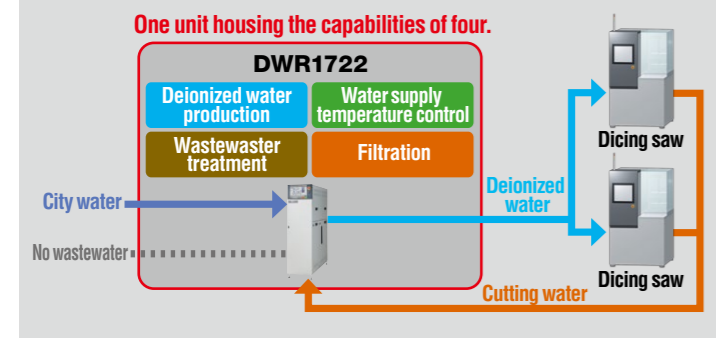
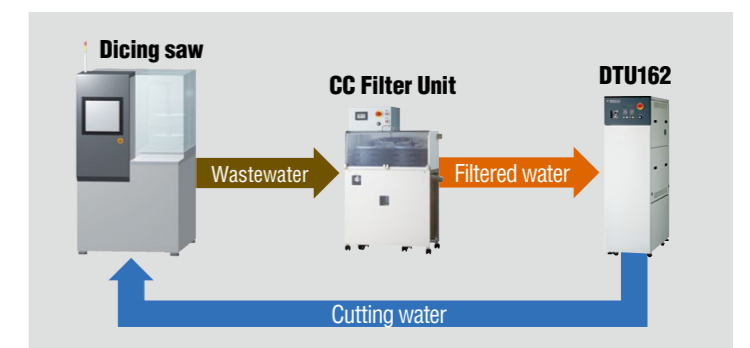
CC Filter Unit

The high-capacity, highly functional CC Filter Unit reduces filtration running costs

- Primary filtration unit to reduce load for cutting water recycling or wastewater treatment.
- Can be combined with the DTU162 to reduce maintenance requirements for cutting water recycling.



		Single	Dual
Water flow rate	L/min	10	20
	Utilities		
Dimensions (WxDxH) mm		400 × 400 × 1,260	760 × 374 × 1,260
	Dry weight kg	Approx. 61	Approx. 75



Cutting Water Additives for Dicing

StayClean-A StayClean-F StayClean-R

Cutting water additives which prevent issues when dicing

- StayClean-A**
 - Prevents particle adhesion
- StayClean-F**
 - Prevents the bonding pads from corroding
 - Prevents particles from adhering to the pad section
- StayClean-R**
 - Prevents the bonding pads from corroding
 - Prevents particles from adhering to the pad section
 - Can be used in combination with a DI water recycling unit (DWR series)



StayClean Injector

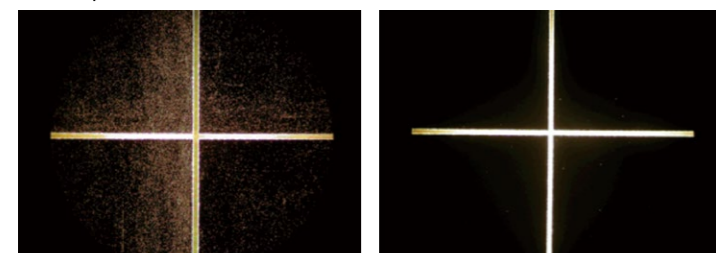
Dedicated unit for injecting StayClean into cutting water

- Highly accurate dilution control to ratios as low as 1:10,000.
- Automatic bottle replacement enables continuous operation.



		StayClean Injector	Bottle Stocker
Flow rate range	L/min	2 - 20	-
	Cutting water temperature °C	20 - 25	-
Controllable concentration %		0.01 - 0.1	-
Utilities	Dimensions (WxDxH) mm	200 × 300 × 500	357 × 392 × 440
	Dry weight kg	Approx. 25	Approx. 10

Reduced particle adhesion

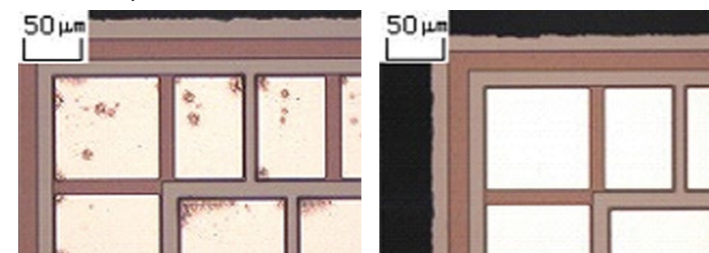


Deionized water

When using StayClean-A

White areas: Adhered particles

Pad corrosion prevention



Deionized water

When using StayClean-F

Resistivity Management Unit for Dicing Saws

CO₂ Injector

Reduces particle adhesion due to charging caused by dicing and device damage caused by static electricity

- Direct control from the dicing saw enables easy operation.
- Applies a multi-stage mixing method to closely track changes in resistivity caused by changes in flow rate.



		Standard specification	Low-resistivity specification
Water flow rate	L/min	0.5 - 1.0	3 - 15
	Resistivity settings range MΩ·cm	0.2 - 0.6	Setting ±10%
Resistivity fluctuation range *		Setting ±0.06 MΩ·cm	
Utilities	Dimensions (WxDxH) mm	328 × 178 × 365	
	Dry weight kg	Approx. 13	

* The flow rate is constant within the range from 3 to 15 L/min at the supply water temperature from 20 to 25°C

